

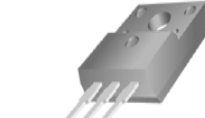
High Voltage NPN Power Transistor

Features

- High Voltage
- High Switch Speed
- $BV_{CEO} : 400V$
- $BV_{CBO} : 700V$
- $I_c : 12A$
- $V_{CE(SAT)} : 2V @ I_c / I_B = 8A / 1.6A$



TO-220
Pin Definition
1. Base
2. Collector
3. Emitter

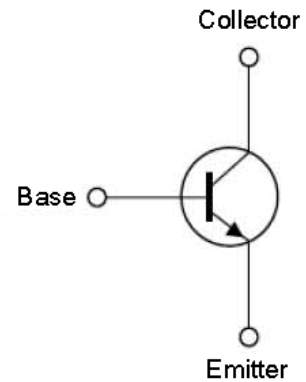


TO-220F
Pin Definition
1. Base
2. Collector
3. Emitter

Application

- Electronic Ballasts
- Adapter
- Lighting

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS ($T_c = 25^\circ C$)

Parameter	Symbol	Max rating	Unit
Collector-Base Voltage	V_{CBO}	700	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	9	V
Collector Current (DC)	I_c	12	A
Collector Current (Pulse)		24	A
Base Current (DC)	I_B	6	A
Total Power Dissipation (TO-220)	P_D	75	W
Total Power Dissipation (TO-220F)	P_D	30	W
Junction Temperature	T_J	+150	$^\circ C$
Operating Junction and Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ C$

Note: Single Pulse. $P_w=300\mu S$, $Duty \leq 2\%$

ELECTRICAL CHARACTERISTICS (T_c = 25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Voltage	BVCBO	IC = 1mA, IB=0	800	—	—	V
Collector-Emitter Breakdown Voltage	BVCEO	IC = 10mA, IE=0	450	—	—	V
Emitter- Base Breakdown Voltage	BVEBO	IE = 1mA, IC=0	9	—	—	V
Collector Cutoff Current	ICEO	VCE = 400V, IB=0	—	—	1	mA
Collector Cutoff Current	ICBO	VCB = 700V, IE=0	—	—	1	mA
Emitter Cutoff Current	IEBO	VEB = 9V, IC=0	—	—	1	mA
DC Current Gain	hFE1	VCE = 5V, IC=5A	15	—	40	
	hFE2	VCE = 5V, IC=8A	5	—	30	
Collector-Emitter Saturation Voltage	VCE(SAT1)	IC = 5A, IB = 1A	—	—	1.2	V
	VCE(SAT2)	IC = 8A, IB =1.6A	—	—	1.6	
Base-Emitter Saturation Voltage	VBE(SAT1)	IC = 5A, IB = 1A	—	—	1.5	V
	VBE(SAT2)	IC = 8A, IB =1.6A	—	—	2	

Dynamic

Frequency	f _T	VCE = 10V, IC=0.5A	4	—	—	MHz
Output Capacitance	C _{ob}	VCB = 10V, f=0.1MHz	—	180	—	pF

Resistive Load Switching Time (Ratings)

Rise Time	t _r	V _{cc} =125V, IC=8A, IB1=1A, IB2=1.6A, tp=25uS Duty Cycle ≤ 2%	—	0.75	1.3	uS
Storage Time	t _{STG}		—	3	5	uS
Fall Time	t _f		—	0.5	0.9	uS

Note: Pulse test: pulse width ≤ 300uS, duty cycle ≤ 2%

Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

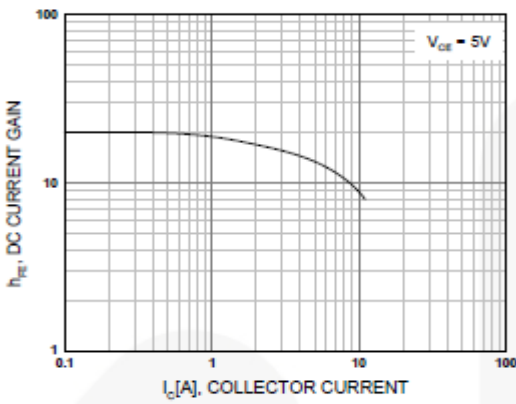


Figure 1. DC Current Gain

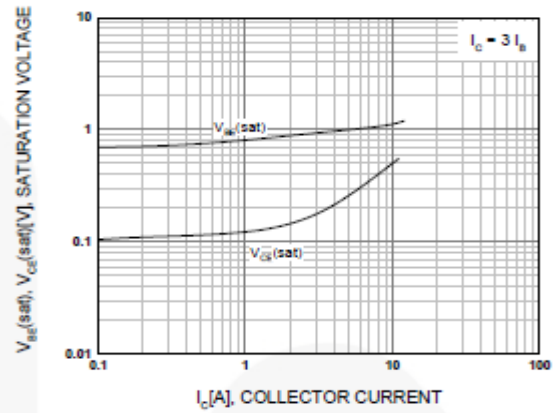


Figure 2. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

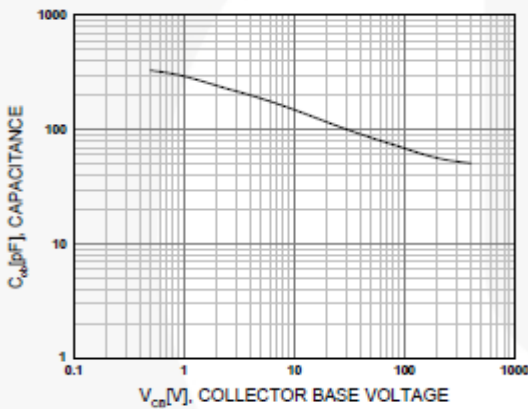


Figure 3. Collector Output Capacitance

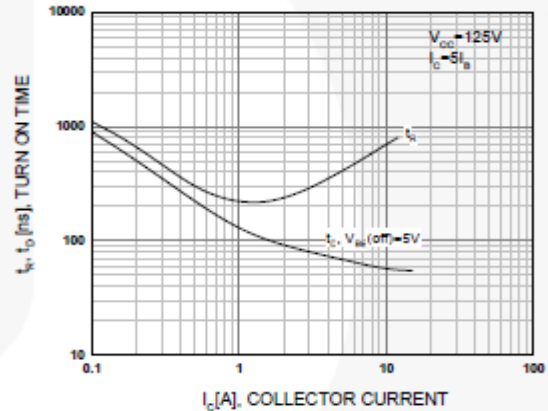


Figure 4. Turn-On Time

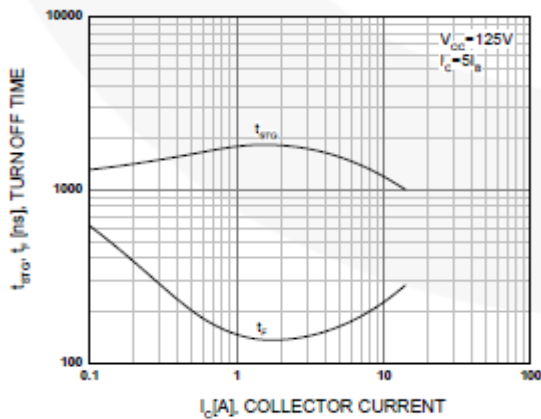


Figure 5. Turn-Off Time

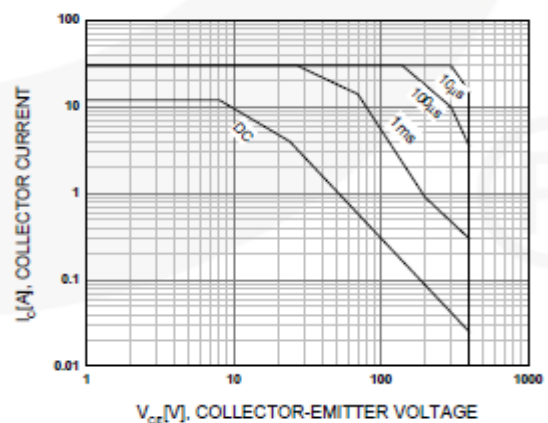


Figure 6. Forward Bias Safe Operating Area

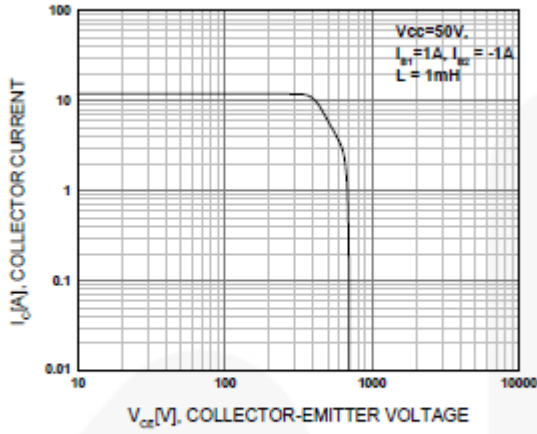


Figure 7. Reverse Bias Safe Operating Area

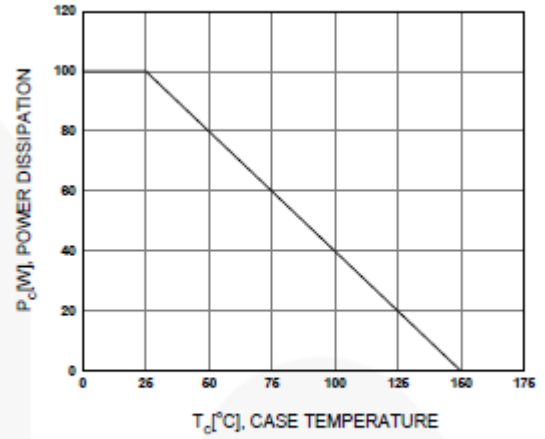
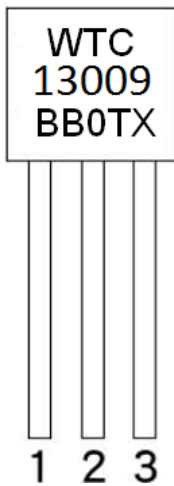


Figure 8. Power Derating

Ordering Information

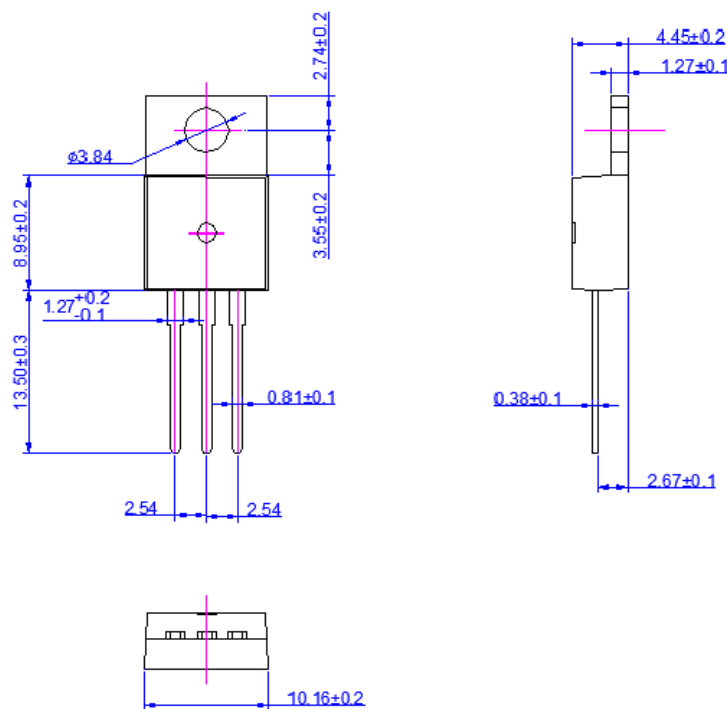
Type NO	Marking	Package Code
WTX13009	13009	TO-220

Marking and Pin Define



First Line	WTC	Company Name	
Second Line	13009	Product Code	
Third Line	BB0TX	1st (Year Code)	A-2010 B-2011 C-2012 D-2013 ...
		2nd (Month Code)	A-Jan, B-Feb, C-Mar, D-Apr, E-May, F-Jun, G-Jul, H-Aug, I-Sep, J-Oct, K-Nov, L-Dec
		3rd (Lot Code)	0~9, A~Z
		4th (Product Code)	M - MOS , T - Transistor, L - Linear
		5th (Package Code)	I - TO251, D - TO252 , L - TO92, M - TO126, X - TO220, F - TO220F, Y - SOT89, S - SOP8
		6th (Spec Code)	(Reserve)

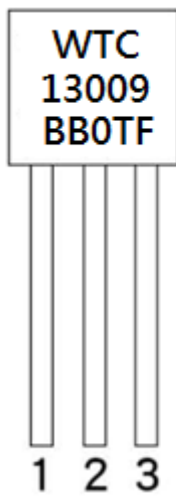
TO-220 Package Dimension



Ordering Information

Type NO	Marking	Package Code
WTF13009	13009	TO-220F

Marking and Pin Define



First Line	WTC	Company Name			
Second Line	13009	Product Code			
Third Line	BB0TF	1st (Year Code)	A-2010 B-2011 C-2012 D-2013 ...		
		2nd (Month Code)	A-Jan, B-Feb, C-Mar, D-Apr, E-May, F-Jun, G-Jul, H-Aug, I-Sep, J-Oct, K-Nov, L-Dec		
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TO-220F Package Dimension

